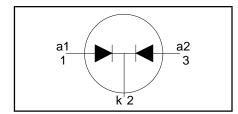
PBYR2545CT, PBYR2545CTB series

FEATURES

- · Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 40 \text{ V} / 45 \text{ V}$$
 $I_{O(AV)} = 30 \text{ A}$
 $V_F \le 0.62 \text{ V}$

GENERAL DESCRIPTION

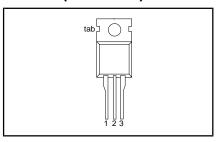
Dual, common cathode schottky rectifier diodes in a conventional leaded plastic package and a surface mounting plastic package. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR2545CT series is supplied in the SOT78 conventional leaded package. The PBYR2545CTB series is supplied in the SOT404 surface mounting package.

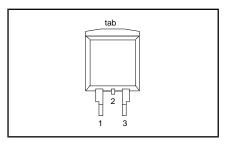
PINNING

PIN	DESCRIPTION		
1	anode 1 (a)		
2	cathode (k) 1		
3	anode 2 (a)		
tab	cathode (k)		

SOT78 (TO220AB)



SOT404



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER CONDITIONS		MIN.	MA	UNIT	
		PBYR25 PBYR25		40CT 40CTB	45CT 45CTB	
V_{RRM}	Peak repetitive reverse voltage		-	40	45	V
V_{RWM}	Working peak reverse voltage		-	40	45	V
V_R	Continuous reverse voltage	T _{mb} ≤ 113 °C	-	40	45	V
I _{O(AV)}	Average rectified forward current (both diodes conducting) ²	square wave; $\delta = 0.5$; $T_{mb} \le 126 ^{\circ}C$	-	30		А
I _{FRM}	Repetitive peak forward current per diode	square wave; $\delta = 0.5$; $T_{mb} \le 126 ^{\circ}C$	-	30)	А
I _{FSM}	Non-repetitive peak forward current per diode	t = 10 ms t = 8.3 ms sinusoidal; T _i = 125 °C prior to	-	180 200		A A
I _{RRM}	Peak repetitive reverse surge current per diode	surge; with reapplied V _{RRM(max)} pulse width and repetition rate limited by T _{i max}	-	1		Α
T _j	Operating junction temperature	i i max	-	15	0	°C
T _{stg}	Storage temperature		- 65	175		°C

1. It is not possible to make connection to pin 2 of the SOT404 package.

2. SOT78 package. For output currents greater than 20A the cathode connection should be made to the metal mounting tab.

PBYR2545CT, PBYR2545CTB series

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb}		per diode	-	-	1.5	K/W
	to mounting base	both diodes	-	-	1	K/W
R _{th j-a}		SOT78 package in free air	-	60	-	K/W
	to ambient	SOT404 package, pcb mounted, minimum footprint, FR4 board	-	50	-	K/W

ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage per diode	$I_F = 20 \text{ A}; T_i = 125^{\circ}\text{C}$ $I_F = 30 \text{ A}; T_i = 125^{\circ}\text{C}$	-	0.58	0.62	V
		$I_F = 30 \text{ A}; T_j = 125 ^{\circ}\text{C}$	-	0.72	0.76	l V
		$I_{\rm F} = 30 \text{ A}$	-	0.72	0.82	V
$ I_R $	Reverse current per diode	$V_R = V_{RWM}$	-	0.3	2	mA
		$V_R = V_{RWM}$; $T_i = 100$ °C	-	30	40	mA
C _d	Junction capacitance per diode	$\dot{V}_{R} = V_{RWM}$ $V_{R} = V_{RWM}$; $T_{j} = 100^{\circ}C$ $V_{R} = 5 \text{ V}$; $f = 1 \text{ MHz}$, $T_{j} = 25^{\circ}C \text{ to } 125^{\circ}C$	1	530	-	pF

PBYR2545CT, PBYR2545CTB series

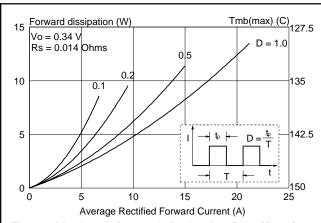


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} x \sqrt{D}$.

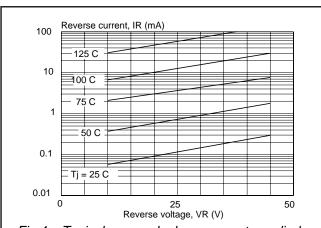


Fig.4. Typical reverse leakage current per diode; $I_R = f(V_R)$; parameter T_j

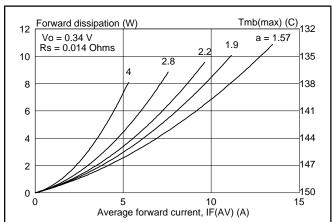


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = f form factor $= I_{F(RMS)} / I_{F(AV)}$.

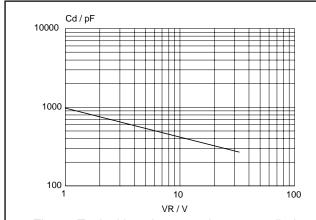


Fig.5. Typical junction capacitance per diode; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25$ °C to 125 °C.

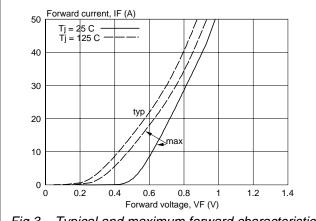


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

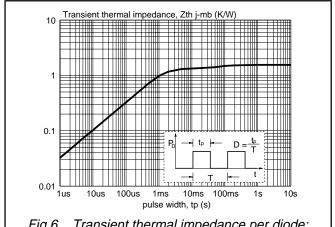
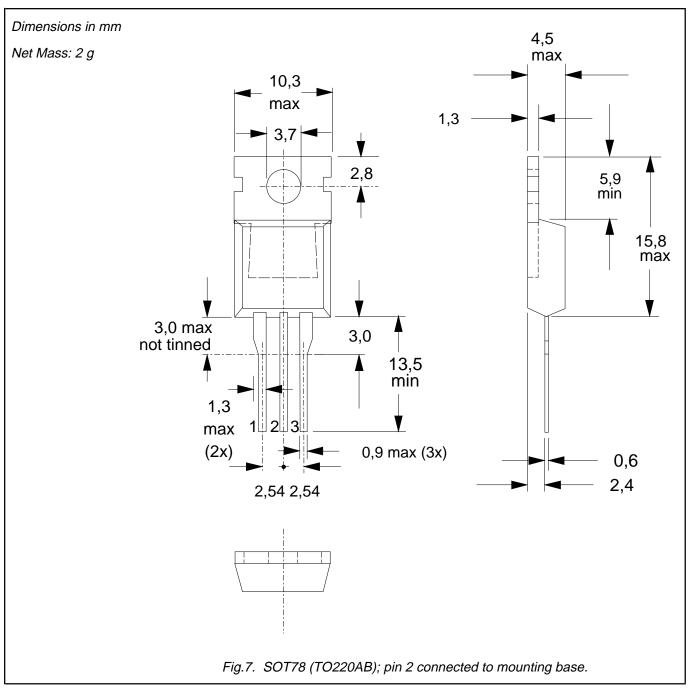


Fig.6. Transient thermal impedance per diode; $Z_{th j-mb} = f(t_p)$.

PBYR2545CT, PBYR2545CTB series

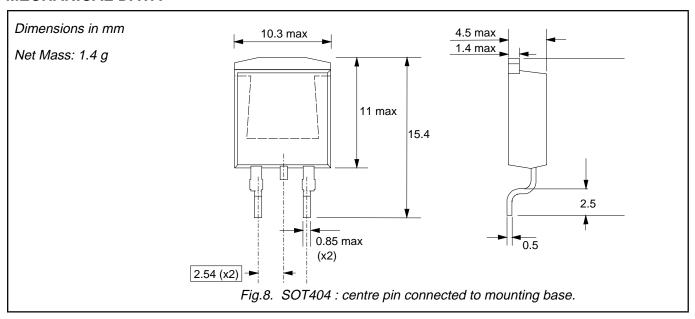
MECHANICAL DATA



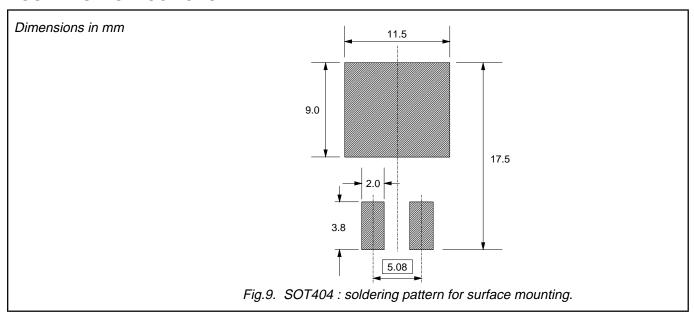
- Refer to mounting instructions for SOT78 (TO220) envelopes.
 Epoxy meets UL94 V0 at 1/8".

PBYR2545CT, PBYR2545CTB series

MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

1. Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Rectifier diodes Schottky barrier

PBYR2545CT, PBYR2545CTB series

DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification This data sheet contains final product specifications.					
Limiting values					

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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